

Electronic Structures of $\text{Fe}_{3-x}\text{V}_x\text{Si}$ Probed by Photoemission Spectroscopy^{**}

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The electronic structures of the Heusler type compounds $\text{Fe}_{3-x}\text{V}_x\text{Si}$ in the concentration range between $x = 0$ and $x = 1$ have been probed by photoemission spectroscopy (PES). The observed shift of Si $2p$ core-level and the main valence band structures indicate a chemical potential shift to higher energy with increasing x . It is also clarified that the density of state at Fermi edge is owing to the collaboration of V $3d$ and Fe $3d$ derived states. Besides the decrease of the spectral intensity near Fermi edge with increasing x suggests the formation of pseudo gap at large x .

1 Introduction

Heusler-type ternary and pseudobinary compounds Y_2ZX (Y and Z denote transition metal atoms and X is a metalloid) have received renewed interest owing to their ferromagnetic shape memory, magneto-resistance properties and thermoelectric power of novel mechanism etc. Among them, $\text{Fe}_{3-x}\text{V}_x\text{Si}$ ($0 \leq x \leq 1$) alloys display a rich variety of physical behavior in electronic, magnetic and transport properties. The ordered Fe_3Si alloy forms D0_3 -type structure (see Fig.1). In the unit cell, there are two in-equivalent Fe sites with specific neighbor configurations named as Fe_I and Fe_{II} . The Fe_I or Si sites are surrounded by eight nearest Fe_{II} atoms in an octahedral configuration, while Fe_{II} site has four Si and four Fe_I nearest neighbors in a tetrahedral configuration. Then, Fe_3Si can be expressed as $[\text{Fe}_I][\text{Fe}_{II}]_2\text{Si}$. Since V lies to the left of Fe in the periodic table of elements, V atoms prefer to occupy Fe_I sites [1]. With increasing vanadium concentration, the crystal structure of $\text{Fe}_{3-x}\text{V}_x\text{Si}$ changes from D0_3 to L2_1 in the concentration range of $0 \leq x \leq 1$.

$\text{Fe}_{3-x}\text{V}_x\text{Si}$ alloys are considered to have relatively high thermoelectric power (TEP) due to a pseudo gap near the Fermi level. Investigation performed by Nishino et al. [2] supports that $\text{Fe}_{3-x}\text{V}_x\text{Si}$ compounds show anomalous resistivity properties including resistance maximum near the Curie point (T_C) and a negative slope of the resistivity above T_C , which increases with adding V atoms. Nashima et al. [3] reported that the compounds show a negative Seebeck coefficient at larger x , which indicates a semimetallic electronic state. The concentration dependence of the Seebeck coefficient on the V content suggests

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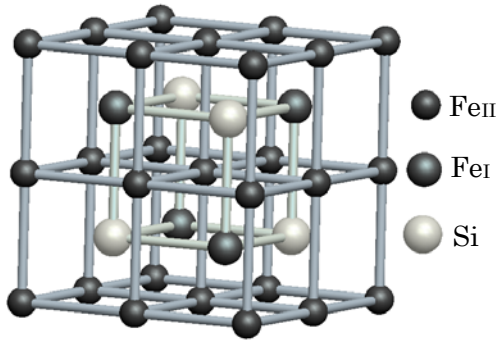


Fig.1 Crystal structure of ordered Fe_3Si

that the substitution of Fe for V in Fe_3Si causes not only the development of the pseudo gap but also a chemical potential shift to higher energy, which are also supported by the theoretical calculations [4, 5]. All of above mentioned physical behaviours could be mainly controlled by the electronic states close to Fermi level (E_F). So, in order to clarify those physical properties of $\text{Fe}_{3-x}\text{V}_x\text{Si}$, it is important to study their electronic structures directly by a photoemission spectroscopy (PES).

In this paper, the electronic structure in the valence band region will be investigated with synchrotron radiation in the vacuum ultraviolet and soft x-ray regions and a core level photoemission spectroscopy is also used to illustrate the chemical potential shift against the V concentration.

2 Experimental

$\text{Fe}_{3-x}\text{V}_x\text{Si}$ polycrystalline samples were prepared by repeated arc-melting of mixtures of Fe, V and Si under purified argon atmosphere. The subsequent post-annealing was performed at 1123 K for 5 days to improve the homogeneity of the alloys. Specimens were cut from the ingots by spark cutting with Cu wire to a size of $1.2 \times 1.2 \times 5 \text{ mm}^3$.

The experiment was carried out with synchrotron radiation in the vacuum ultraviolet (VUV) and soft X-ray regions. The VUV photoemission spectroscopy (VUV-PES) was measured with a hemispherical analyzer at BL-7 of Hiroshima Synchrotron Radiation Center (HSRC). The soft X-ray photoelectron spectroscopy (SX-PES) was also measured at the undulator beamline BL-23SU of SPring-8. The angle between the incident photon beam and the lens axis of the analyzer was 45° . The acceptance angle of the analyzer was set to $\pm 8^\circ$. The Fermi energy and the total energy resolution were checked with the evaporated Au film. The evaluated total energy resolutions for the VUV photoemission at 50 K were 54 meV and 190 meV for the photon energies ($h\nu$) of 38 eV and 146 eV, respectively. For the soft X-ray photoemission at room temperature the total energy resolution was 300 meV for $h\nu = 1030 \text{ eV}$.

Clean surfaces of the specimens were obtained by in situ fracturing with a knife edge, and they were confirmed by the O $1s$ core level for the SX-PES as well as the O $2p$ signal in the valence band for VUV-PES.

3 Result and discussion

The Si $2p$ core level spectra have been measured at $h\nu = 146 \text{ eV}$ (see Fig.2). We plot the binding energies of $2p_{3/2}$ and $2p_{1/2}$ main peaks as a function of x in Fig.3. It is clearly found that the Si $2p$ main peaks shift to higher binding energy with increasing x . The observed core-level shift is possibly due to a chemical potential shift to higher energy. There would also be another possibility of a chemical shift due to a different environment of Si atom with different vanadium concentration. However, since the V atom prefers to occupy the Fe_I site, the Si atom is still surrounded by 8 Fe_{II} atoms while keeping the environment of Si, then the chemical shift should be excluded. Besides the Si $2p$ main peaks, there is a somewhat broad structure at lower binding energy, it is also recognized that the Si $2p$ main peaks are broader for the larger x , which might come from an atomic disorder at the surface or inside the crystal. In order to

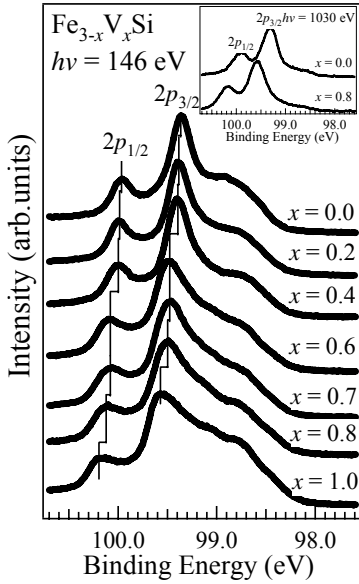


Fig.2 Si 2p core-level photoemission spectra of $\text{Fe}_{3-x}\text{V}_x\text{Si}$ with $x = 0\sim 1$ measured at $h\nu = 146$ eV.

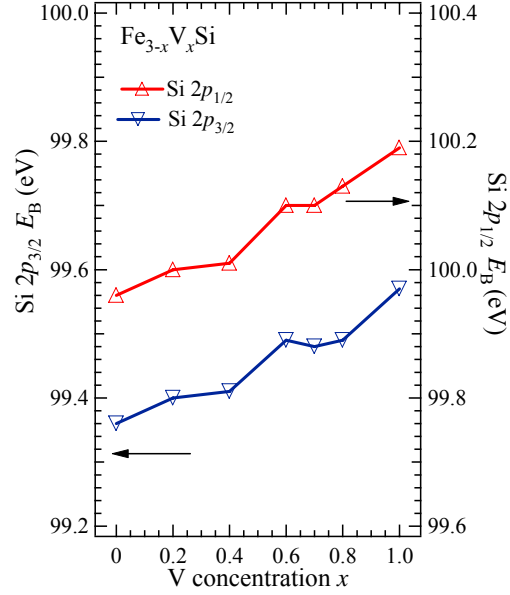


Fig.3 Binding energies of Si $2p_{3/2}$ and $2p_{1/2}$ main peaks vs. x .

find the origin of these additional structures, the Si 2p core-level spectra have been measured again using soft x-ray ($h\nu = 1030$ eV) at room temperature (for $x = 0$ and 0.8) and are plotted in the inset of Fig.2. Note that the additional structures at low binding energy are markedly reduced in the SX-PES spectra. This result indicates that they are mainly due to the surface effect if we take into account the shorter electron mean-free path for the electrons with smaller kinetic energy.

The valence band spectra measured at $h\nu = 38$ eV and $T = 50$ K with different x are shown in Fig.4. We find two sharp peaks denoted as A (just below E_F) and C (at 1.5 eV below E_F) for $x = 0$. It is noticed that the structure C shifts to higher binding energy (E_B) and is less weighted with increasing x . Besides, the intensity of peak A is also gradually reduced and the peak position does not change toward larger x . For $x > 0.4$, the peak B develops around 1 eV and it becomes sharper and shifts to larger E_B with increasing x . In order to assign these main structures, the valence band spectra taken at the different photon energies for $x = 0$ and 0.8 are compared in Fig.5. It implies that the intensities at E_F are enhanced in the VUV-PES spectra for both $x = 0$ and 0.8 compared to those in the SX-PES spectra, which are more bulk sensitive. In Fig.5, the photoemission intensities for the structures E and F are enhanced at the higher photon energy.

By taking into account the photoionization cross section, some structures can be separated into different component contributions, because the cross section of V $3d$ state decreases faster than that of Fe $3d$ state, while that of Si $3p$ state decreases more moderately than that of Fe $3d$ state with increasing photon energy. It is considered that the structures E and F should be Si $3p$ and Si $3s$ derived states, respectively. The spectral intensity at E_F for $x = 0.8$ is much reduced with increasing photon energy compared to that for $x = 0$, which means the density of states at E_F should be mainly owing to the contribution of V $3d$ state for large x . The structure B emerges and enhanced with adding V atoms at $h\nu = 38$ eV, which should be related to the V $3d$ states. While for $x = 0.8$, with increasing $h\nu$, the spectral intensity of the structure B does not change so much as that at E_F , which means it is mainly due to the contribution of Fe $3d$ states. Although it seems difficult for the structure D to be assigned only from the cross section,

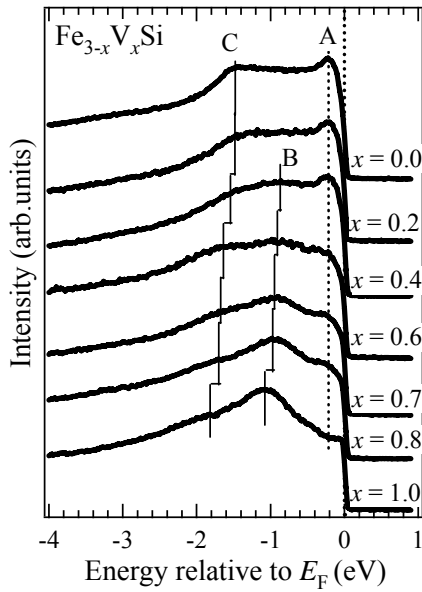


Fig.4 Valence band photoemission spectra of $\text{Fe}_{3-x}\text{V}_x\text{Si}$ with photon energy ($h\nu$) of 38 eV at 50 K. The black dotted lines are just for the guide to the eye.

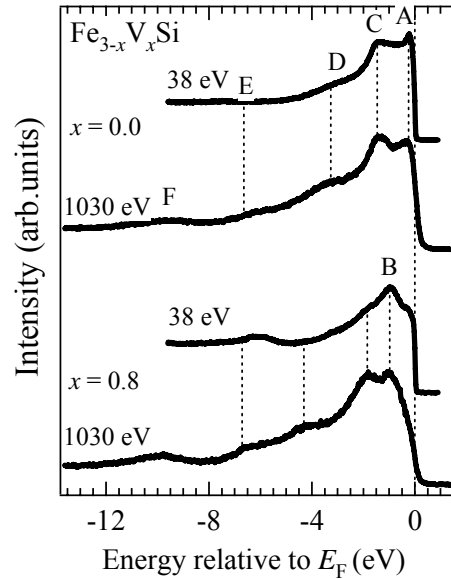


Fig.5 Valence band photoemission spectra of $\text{Fe}_{3-x}\text{V}_x\text{Si}$ with $x = 0.0$ and 0.8 measured at $h\nu = 38$ eV and 1030 eV.

this may be due to a bonding state of Si $3p$ orbital with Fe $3d$ or V $3d$ orbitals. The observed shift of the structures B and C to higher binding energy is another evidence for the chemical potential shift. In Fig.6, it can also be seen that the intensity of the spectra below E_F is reduced with increasing V concentration especially for $x > 0.6$. That might be related to the formation of the pseudo gap at large x as pointed out by the theoretical calculation [4, 5] and the experiment [3].

4 Conclusion

In conclusion, the valence band and Si $2p$ core-level photoemission spectra of $\text{Fe}_{3-x}\text{V}_x\text{Si}$ ($0 \leq x \leq 1$) have been measured with synchrotron radiation in the vacuum ultraviolet and soft X-ray regions. The observed energy shift of Si $2p$ core-level and the main valence band structures to higher binding energy with increasing x is due to the chemical potential shift to higher energy with increasing V concentration. The features observed at 1 eV and 1.5~1.8 eV for several x have been assigned to the Fe $3d$ derived state by taking into account the photoionization cross section. It has also been clarified that the spectral intensity at the Fermi level consists of both V $3d$ and Fe $3d$ derived states. The decrease of the spectral intensity near E_F with increasing x suggests the formation of pseudo gap at large x .

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